



# YJL3134KAT

## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	20 V
$I_D$	0.5 A
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	300 mohm
$R_{DS(ON)}$ ( at $V_{GS}=2.5V$ )	400 mohm
$R_{DS(ON)}$ ( at $V_{GS}=1.8V$ )	700 mohm
ESD Protected Up to 2.0KV (HBM)	

### General Description

Trench Power LV MOSFET technology  
High Power and current handing capability

### Applications

PWM application  
Load switch

### Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit
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## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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YJ



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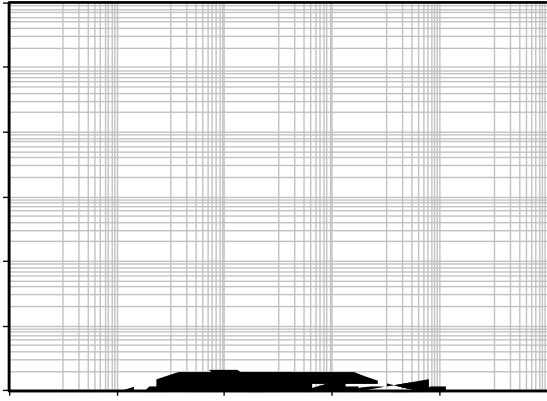


Figure 13. Maximum Transient Thermal Impedance

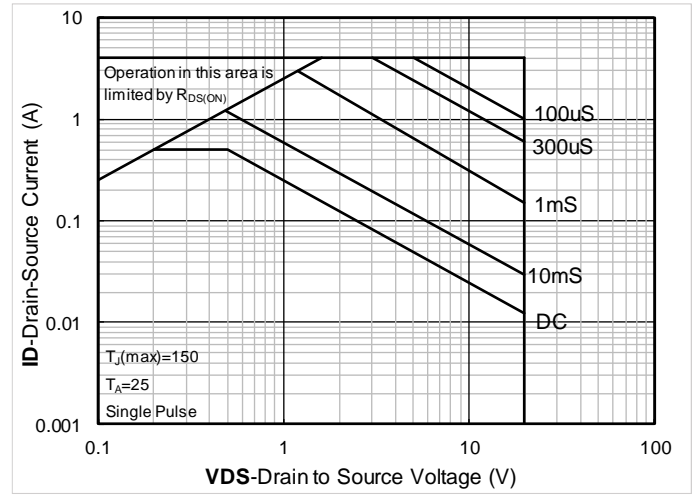


Figure14. Safe Operation Area

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